

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

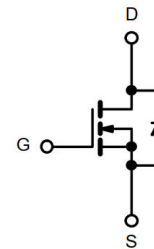
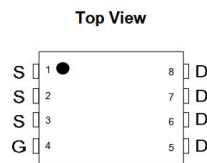
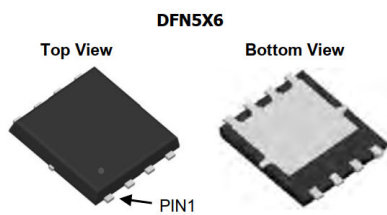
V_{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I_D (A) ^{a, e}	Q_g (Typ.)
60	1.8 at $V_{GS} = 10$ V	180	105 nC
	2.8 at $V_{GS} = 4.5$ V		

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- Notebook PC Core
- VRM/POL



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Pulsed Drain Current	I_{DM}	720	mJ
Avalanche Current Pulse	I_{AS}	175	
Single Pulse Avalanche Energy	E_{AS}	650	
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	A
		$T_A = 25$ °C	
Maximum Power Dissipation	P_D	$T_C = 25$ °C	W
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	18	25	°C/W
Maximum Junction-to-Case	R_{thJC}	0.6	0.8	

Notes:

- a. Based on $T_C = 25$ °C.
b. Surface mounted on 1" x 1" FR4 board.
c. $t = 10$ s.
d. Maximum under steady state conditions is 90 °C/W.
e. Calculated based on maximum junction temperature.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA	-	35	-	mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J		-	- 5.5	-	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0		3.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-		± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	-		1	μA
		V _{DS} =60 V, V _{GS} = 0 V, T _J = 55 °C	-		10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	180			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	1.8	2.5	mΩ
		V _{GS} = 4.5 V, I _D = 30 A	-	2.8	3.6	
Forward Transconductance ^a	g _{fs}	V _{DS} = 5 V, I _D = 20 A	-	110		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} =30 V , V _{GS} = 0 V, f = 1 MHz	-	7080	-	pF
Output Capacitance	C _{oss}		-	1440	-	
Reverse Transfer Capacitance	C _{rss}		-	3	-	
Total Gate Charge	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 30 A	-	105	-	nC
Gate-Source Charge	Q _{gs}		-	84	-	
Gate-Drain Charge	Q _{gd}		-	16	-	
Gate Resistance	R _g	f = 1 MHz	-	1.5	-	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30 V, R _L = 0.555Ω I _D =30 A, V _{GEN} = 10 V, R _g = 1Ω	-	19	-	ns
Rise Time	t _r		-	20	-	
Turn-Off Delay Time	t _{d(off)}		-	31	-	
Fall Time	t _f		-	6	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-		180	A
Pulse Diode Forward Current ^a	I _{SM}		-		720	
Body Diode Voltage	V _{SD}	I _S = 20 A	-	0.8	1.2	
V Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C	-	55	78	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	97	170	nC
Reverse Recovery Fall Time	t _a		-	29		ns
Reverse Recovery Rise Time	t _b		-	23		

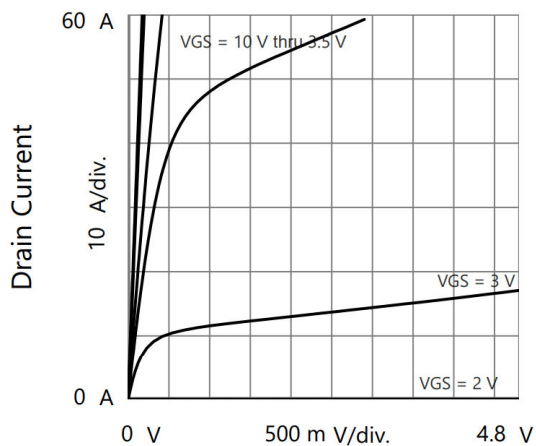
Notes:

 a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

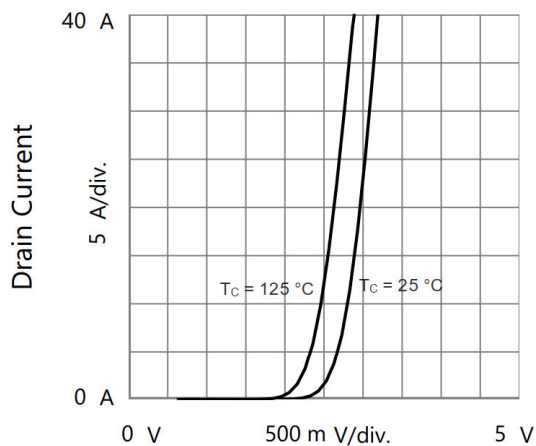
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

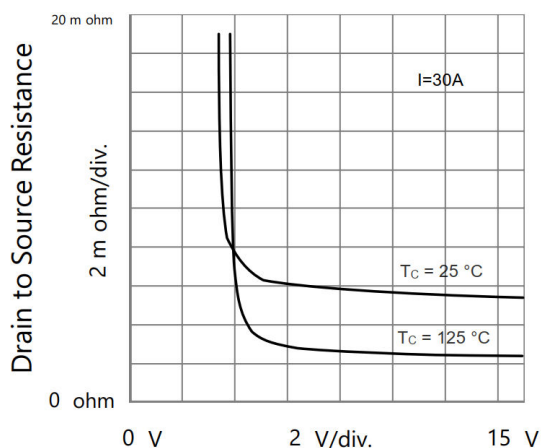
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



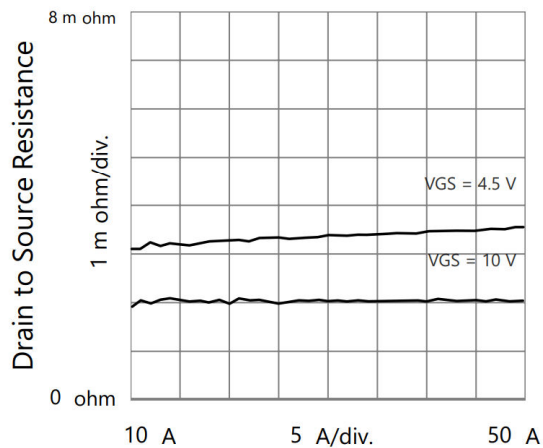
Drain to Source Voltage
Output Characteristics



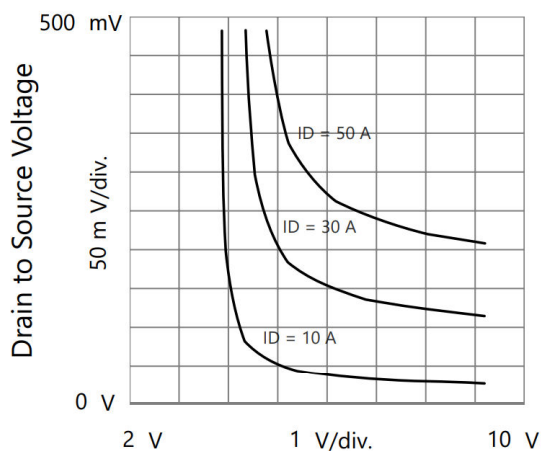
Gate to Source Voltage
Transfer Characteristics



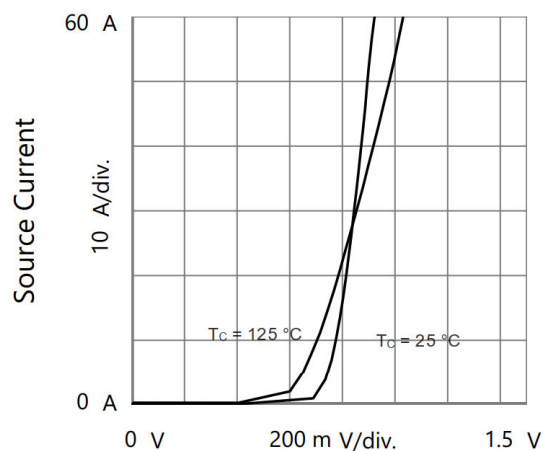
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

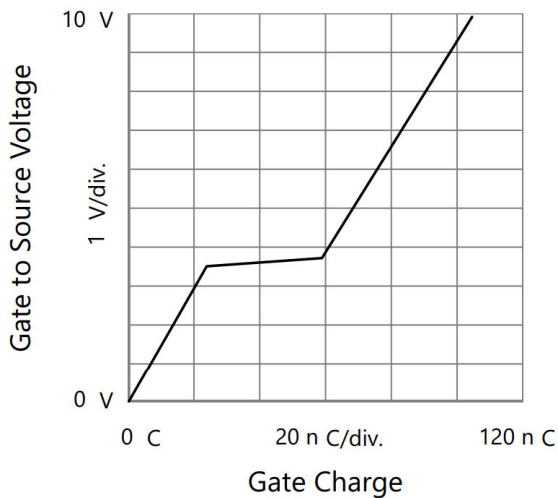


Gate to Source Voltage
Drain to Source Voltage vs. Gate to Source Voltage

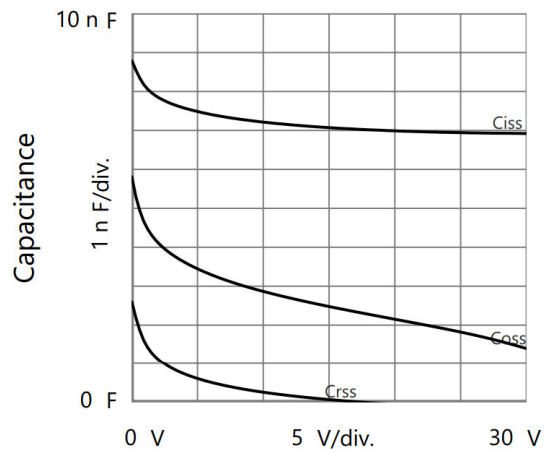


Source to Drain Voltage
Body Diode Forward Characteristics

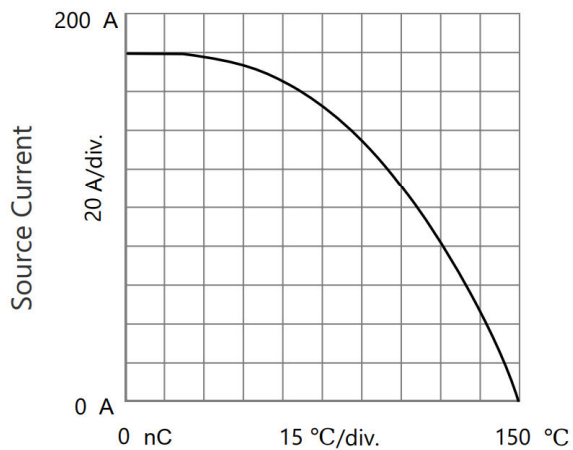
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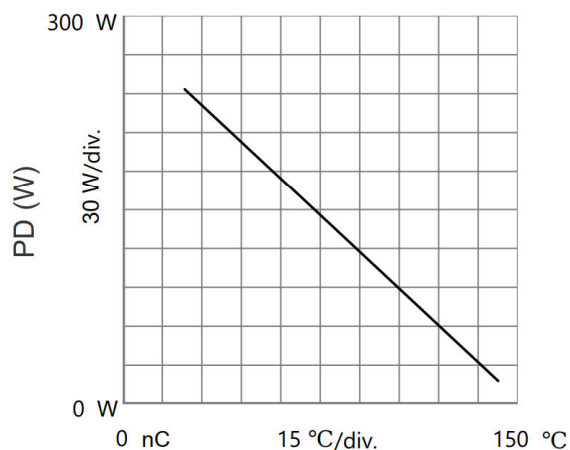
Gate to Source Voltage vs. Gate Charge



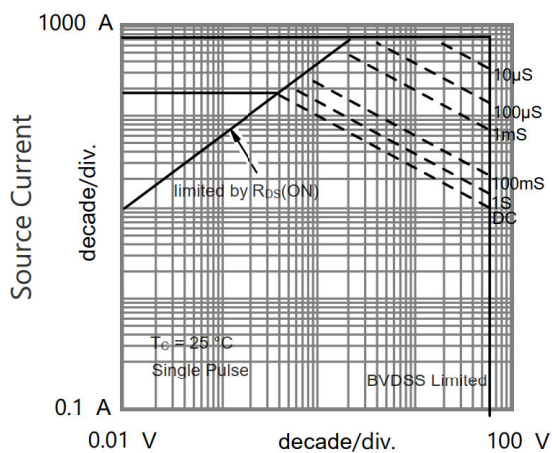
Drain to Source Voltage Capacitances



T_C - Case Temperature
Current Derating



T_C - Case Temperature
Power Derating



Source to Drain Voltage
Safe Operating Area, Junction-to-Ambient

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